



(12) **CORRECTED EUROPEAN PATENT SPECIFICATION**

(15) Correction information:
Corrected version no 2 (W2 B1)
Corrections, see
Bibliography INID code(s) 72, 73

(48) Corrigendum issued on:
23.02.2022 Bulletin 2022/08

(45) Date of publication and mention
of the grant of the patent:
17.11.2021 Bulletin 2021/46

(21) Application number: **14820214.6**

(22) Date of filing: **03.07.2014**

(51) International Patent Classification (IPC):
H01L 21/18^(2006.01) H01L 21/20^(2006.01)
H01L 21/762^(2006.01) H01L 29/16^(2006.01)

(52) Cooperative Patent Classification (CPC):
H01L 21/02002; H01L 21/187; H01L 21/2007;
H01L 21/76254; H01L 29/1608

(86) International application number:
PCT/JP2014/067777

(87) International publication number:
WO 2015/002266 (08.01.2015 Gazette 2015/01)

(54) **MANUFACTURING METHOD FOR SEMICONDUCTOR SUBSTRATE**
VERFAHREN ZUR HERSTELLUNG EINES HALBLEITERSUBSTRATS
PROCÉDÉ DE FABRICATION D'UN SUBSTRAT SEMI-CONDUCTEUR

(84) Designated Contracting States:
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB
GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO
PL PT RO RS SE SI SK SM TR

(30) Priority: **05.07.2013 JP 2013142151**

(43) Date of publication of application:
11.05.2016 Bulletin 2016/19

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